Abstracts

A New Method for On-Wafer High Frequency Noise Measurement of FET's

G. Dambrine, A. Cappy and E. Delos. "A New Method for On-Wafer High Frequency Noise Measurement of FET's." 1991 MTT-S International Microwave Symposium Digest 91.1 (1991 Vol. I [MWSYM]): 169-172.

A new method for determining the equivalent noise resistance Rn and the magnitude of the optimum generator admittance |Yopt| is described. This method is based on the fact that the real part of the correlation admittance can be neglected. A new method for determining the other noise parameters Gamma opt and Fmin without automatic input tuner is then proposed.

❑ Return to main document.